

Product specifications

Silicon carbide puck specification	
Property	Value
Polytype	4H polytype
Orientation	4° offcut
Diameter	200 ±0.05mm
Thickness	6.5mm
Warp	<25µm
TTV	<4 µm
Surface treatment (Si-face)	Epi-ready
Resistivity	19.5-20.5 mΩ.cm
Resistivity uniformity	<2%
Edge exclusion	3 mm

Defect density	
Property	Value
Micropipes (MP)	<2 on wafer
Basal plane dislocation density (BPD)	<70 on wafer
Threading screw dislocation density (TSD)	<100 cm ⁻²
Threading edge dislocation density (TED)	<800 cm ⁻²
Etch pit density (EPD)	<1'000 cm ⁻²

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